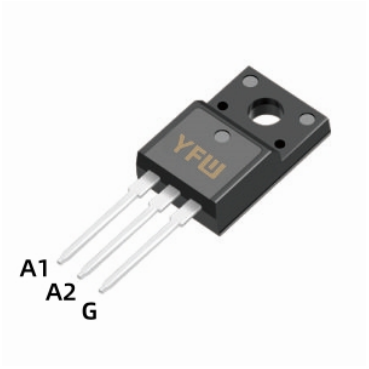
8A 4Quadrants TRIACs

Product Summary

Symbol	Value	Unit
$I_{T(RMS)}$	8	A
V_{DRM} V_{RRM}	600/800	V
V_{TM}	1.55	V



TO-220F

Features

With high ability to withstand the shock loading of large current, Provide high dv/dt rate with strong resistance to electromagnetic interference.

Application

Power charger, T-tools, massager, solid state relay, AC Motor speed regulation and so on.

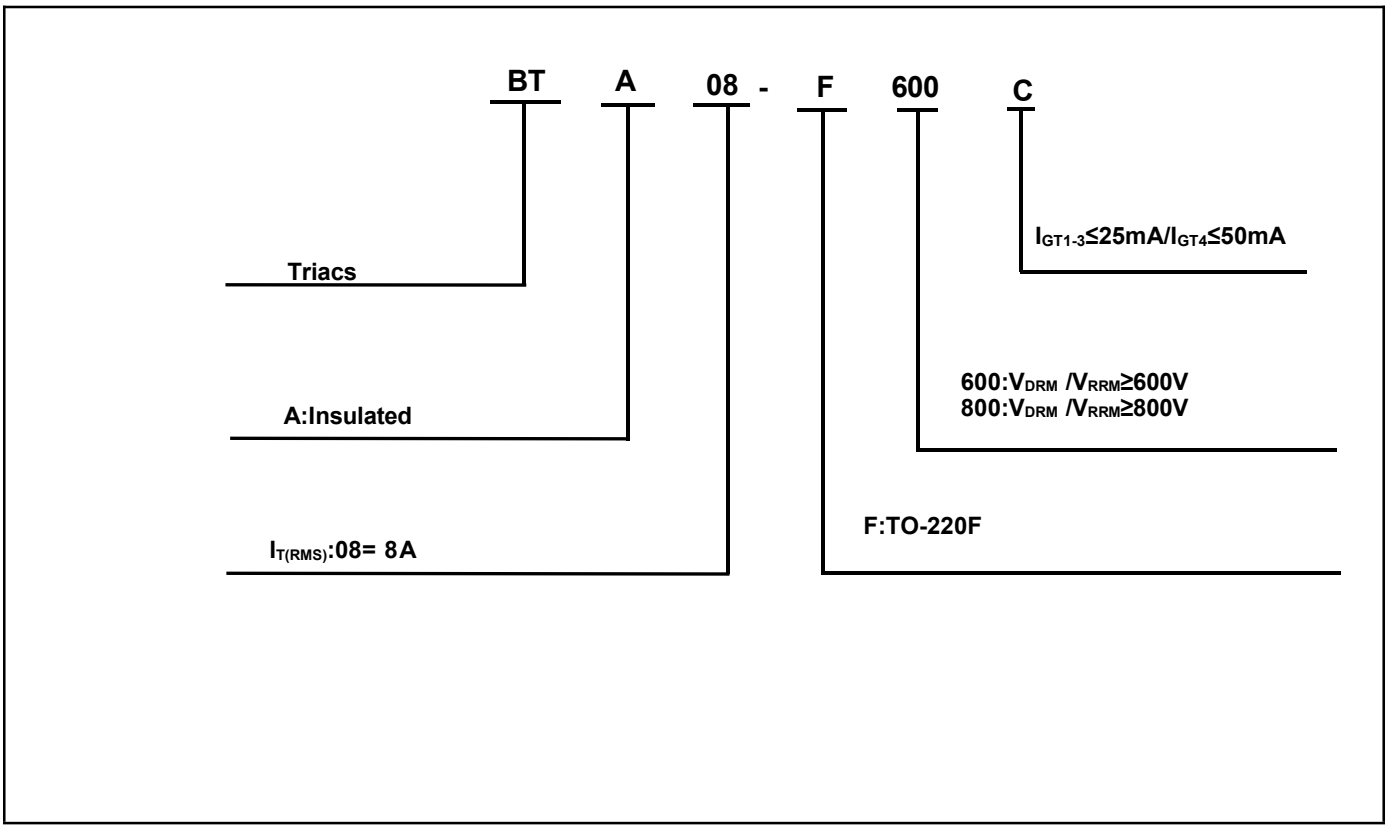
Absolute maximum ratings (Ta=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Repetitive peak off-state voltage	V_{DRM}	600/800	V
Repetitive peak reverse voltage	V_{RRM}	600/800	V
RMS on-state current	$I_{T(RMS)}$	8	A
Non repetitive surge peak on-state current (F=50Hz t=20ms/F=60Hz t=16.7ms)	I_{TSM}	84/80	A
I^2t value for fusing (tp=10ms)	I^2t	32	A^2s
Critical rate of rise of on-state current (I_G =2 x I_{GT})	dI/dt	I - II - III 50	A/μs
Peak gate current	I_{GM}	2	A
Average gate power dissipation	$P_{G(AV)}$	0.5	W
Junction Temperature	T_J	-40~+110	°C
Storage Temperature	T_{STG}	-40 ~+150	°C

Electrical characteristics (T_A=25°C, unless otherwise noted)

Parameter	Symbol	Test Condition		Value C	Unit
Gate trigger current	I_{GT}	V_D=12V, R_L=30Ω	Ⅰ-Ⅱ-Ⅲ	25	mA
			Ⅳ	50	mA
Gate trigger voltage	V_{GT}		ALL	1.5	V
Non-triggering gate voltage	V_{GD}	V_D=V_{DRM},R_L=3.3kΩ,T_j=125°C	ALL	0.2	V
Holding current	I_H	I_T=500mA	ALL	50	mA
Latching current	I_L	I_G=1.2I_{GT}	Ⅰ-Ⅱ-Ⅳ	30	mA
			Ⅱ	60	
Critical-rate of rise of commutation voltage	dV/dt	V_D=67%V_{DRM},gate open T_j=110℃		10	V/μs
STATIC CHARACTERISTICS					
On-state Voltage	V_{TM}	I_T=11A,t_p=380μs	T_j = 25°C	1.55	V
Repetitive Peak Off-State Current	I_{DRM}	V_D=V_{DRM}= V_{RRM}	T_j=25℃	10	μA
Repetitive Peak Reverse Current	I_{RRM}		T_j=110℃	1	mA
THERMAL RESISTANCES					
Ihermal resistance	$R_{th\ (j-c)}$	Junction to case	TYP.	3.3	℃/W
	$R_{th\ (j-a)}$	Junction to ambient	TYP.	60	℃/W

Ordering Information



Typical Characteristics

FIG.1: Maximum power dissipation versus RMS on-state current (full cycle)

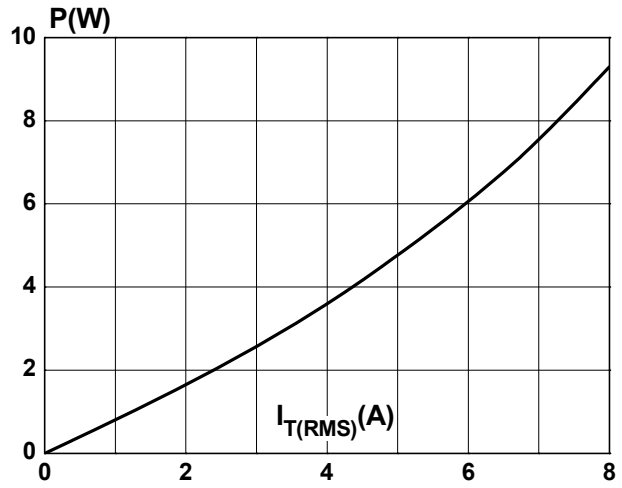


FIG.2: RMS on-state current versus case temperature (full cycle)

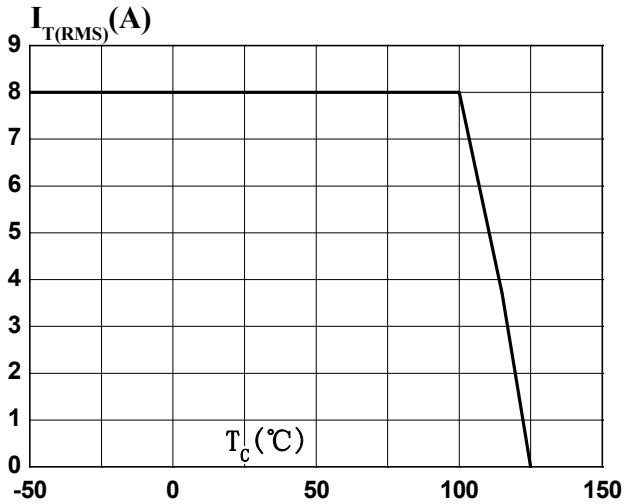


FIG.3: Surge peak on-state current versus number of cycles

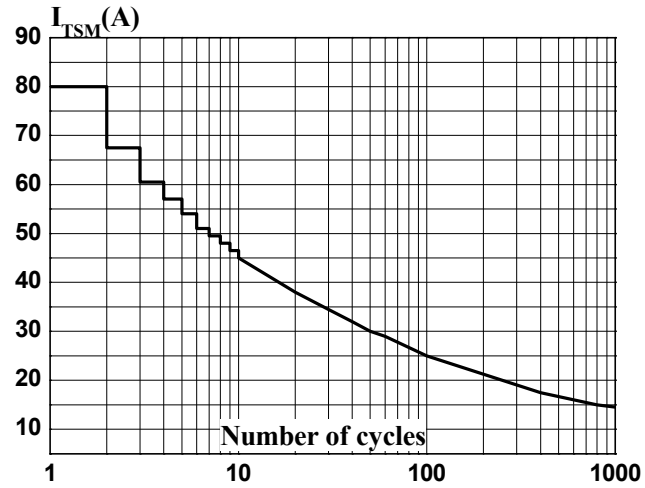


FIG.4: On-state characteristics (maximum values)

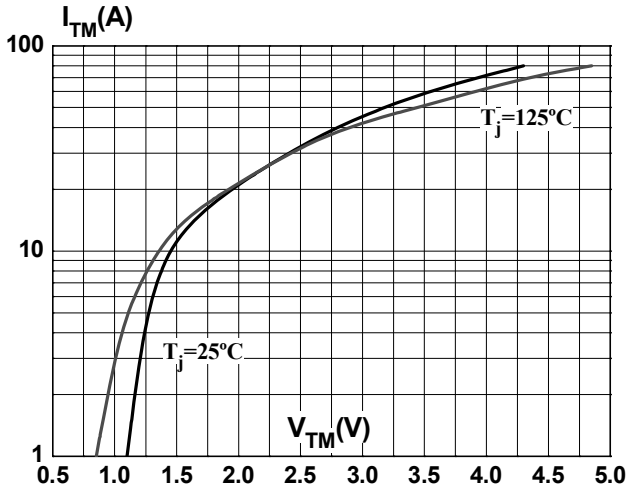


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width tp < 10ms

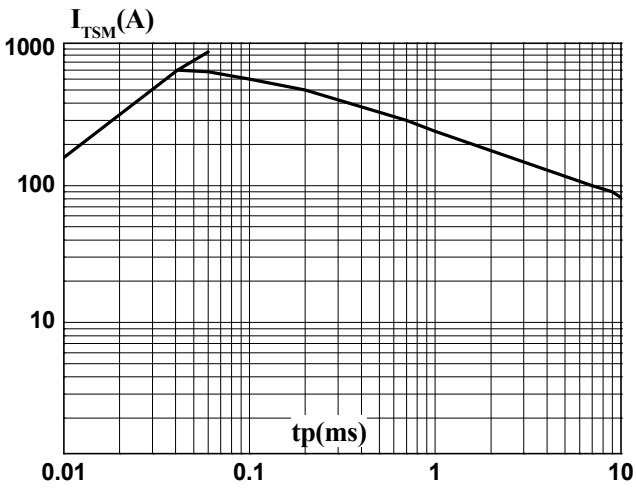
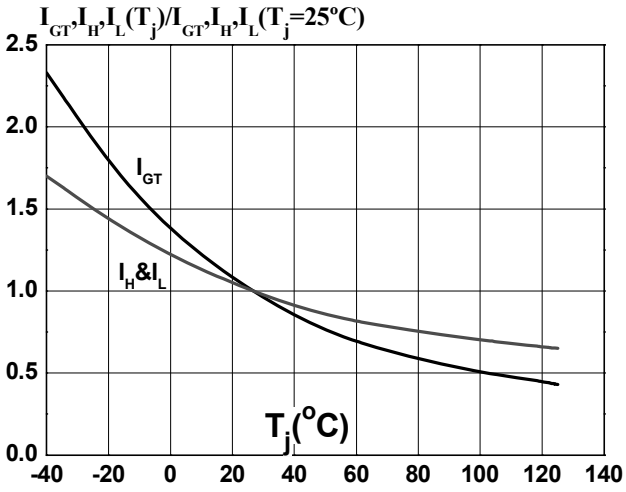
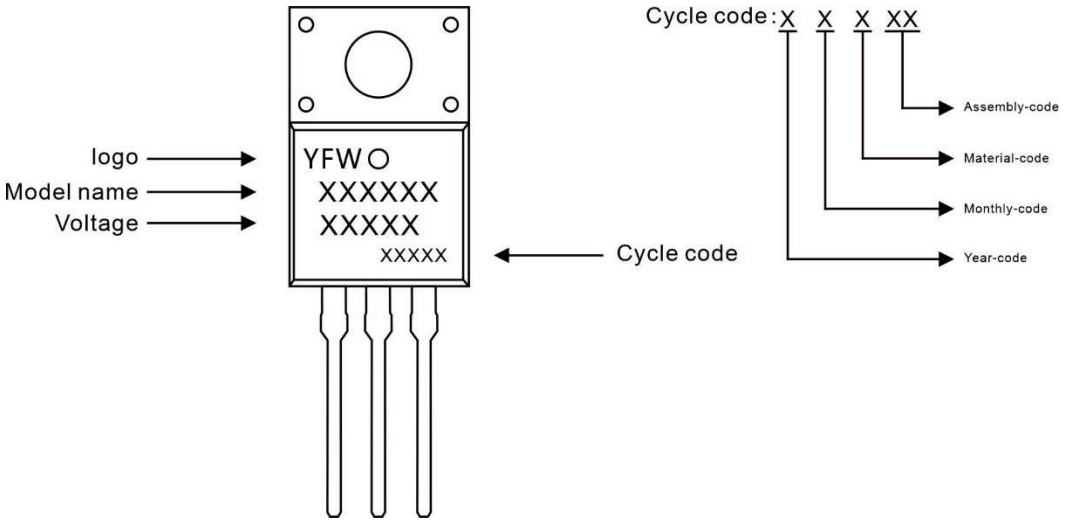


FIG.6: Relative variations of gate trigger current, holding current and latching current versus junction



Marking Diagram

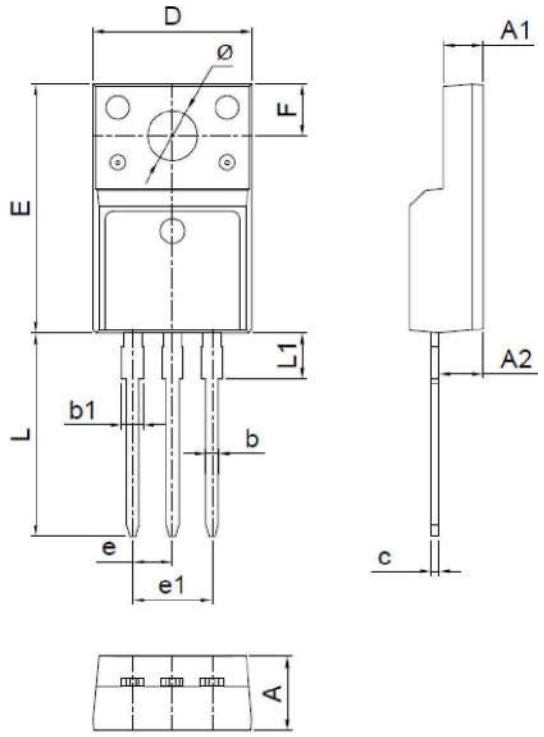


Ordering information

Model name	Package	Unit Weight	Base Quantity	Packing Quantity
BTA08F	TO-220F	0.06oz(1.74g)	50pcs/tube	1000PCS/Box 5000PCS/Carton

Package Dimensions

TO-220F



Symbol	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.50	4.90	0.177	0.193
A1	2.34	2.74	0.092	0.108
A2	2.66	2.86	0.105	0.113
b	0.75	0.85	0.030	0.033
b1	1.24	1.44	0.049	0.057
c	0.40	0.60	0.016	0.024
D	10.00	10.32	0.394	0.406
E	15.75	16.05	0.620	0.632
e	2.44	2.64	0.096	0.104
e1	4.88	5.28	0.192	0.208
F	3.10	3.5	0.122	0.138
L	13.50	13.90	0.531	0.547
L1	2.90	3.30	0.114	0.130
Φ	3.10	3.30	0.122	0.130

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